

Integrated Device Technology, Inc.

**CMOS PARALLEL** FIRST-IN/FIRST-OUT FIFO 256 x 9-BIT, 512 x 9-BIT, 1K x 9-BIT

IDT7200S/L IDT7201SA/LA IDT7202SA/LA T-46-35

#### **FEATURES:**

- First-In/First-Out dual-port memory
- 256 x 9 organization (IDT7200)
- 512 x 9 organization (IDT7201A) 1K x 9 organization (IDT7202A)
- Low power consumption
  - Active: 770mW (max.)
- —Power-down: 27.5mW (max.)
  Ultra high speed—15ns access time
- Asynchronous and simultaneous read and write
- Fully expandable by both word depth and/or bit width
- Pin and functionally compatible with 720X family Status Flags: Empty, Half-Full, Full
- Auto-retransmit capability
- High-performance CEMOS™ technology
- Military product compliant to MIL-STD-883, Class B
- Standard Military Drawing #5962-87531, 5962-89666, 5962-89863 and 5962-89536 are listed on this function.

### **DESCRIPTION:**

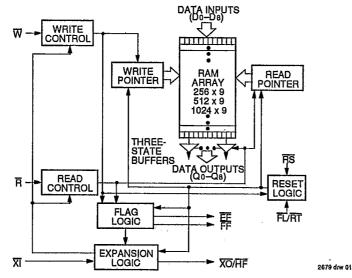
The IDT7200/7201A/7202A are dual-port memories that load and empty data on a first-in/first-out basis. The devices use Full and Empty flags to prevent data overflow and underflow and expansion logic to allow for unlimited expansion capability in both word size and depth.

The reads and writes are internally sequential through the use of ring pointers, with no address information required to load and unload data. Data is toggled in and out of the devices through the use of the Write  $(\overline{W})$  and Read  $(\overline{R})$  pins. The devices have a read/write cycle time of 25ns (40MHz).

The devices utilizes a 9-bit wide data array to allow for control and parity bits at the user's option. This feature is especially useful in data communications applications where it is necessary to use a parity bit for transmission/reception error checking. It also features a Retransmit (RT) capability that allows for reset of the read pointer to its initial position when RT is pulsed low to allow for retransmission from the beginning of data. A Half-Full Flag is available in the single device mode and width expansion modes.

The IDT7200/7201A/7202A are fabricated using IDT's high-speed CEMOS technology. They are designed for those applications requiring asynchronous and simultaneous read/ writes in multiprocessing and rate buffer applications. Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B.

# **FUNCTIONAL BLOCK DIAGRAM**



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**MILITARY AND COMMERCIAL TEMPERATURE RANGES** 

**APRIL 1992** 

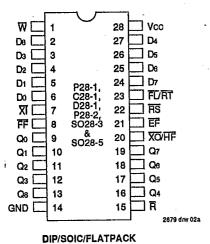
O1992 Integrated Device Technology, Inc.

DSC-2000/4

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2679 dry 025

## PIN CONFIGURATIONS



INDEX 4 3 2 1 32 31 30 29 E D<sub>6</sub> D2 D1 6 28 **D**7 27 E NC Do X FL/RT J32-1 26 8 FF & L32-1 RS 25 🗆 9 酻 Qo 24 🗆 10 آ XO/HF 23 [ Q1 7 11 22 E Q7 NO **]** 12 Q6 Q2 **]** 13 21 [ 14 15 16 17 18 19 20 S 1E 4 8

> LCC/PLCC **TOP VIEW**

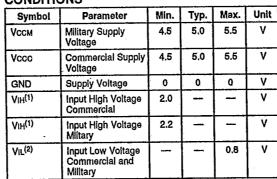
# ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Com'l.	MII.	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	٧
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	65 to +135	°C
Тѕта	Storage Temperature	-55 to +125	-65 to +155	°C
lout	DC Output Current	50	50	mA

**TOP VIEW** 

NOTE:

# RECOMMENDED DC OPERATING CONDITIONS



NOTE:

2679 tbl 02

5.1

1. ViH = 2.6V for XI Input (commercial).

ViH = 2.8V for XI Input (military).

2. 1,5V undershoots are allowed for 10ns once per cycle.

## CAPACITANCE (TA = +25°C, f = 1.0 MHz)

Symbol	Parameter <sup>(1)</sup>	Condition	Max.	Unit
CIN	Input Capacitance	VIN ≈ 0V	8	ρF
Cour	Output Capacitance	Vout = 0V	8	ρF

NOTE: 1. This parameter is sampled and not 100% tested.

2

2879 tbl 03

<sup>1.</sup> Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

47E D

4825771 0009418 9 MMIDT

IDT7200/7201A/7202A CMOS PARALLEL FIRST-IN/FIRST-OUT FIFO 256 x 9-BiT, 512 x 9-BiT & 1K x 9-BiT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

# DC ELECTRICAL CHARACTERISTICS

(Commercial: Vcc = 5.0V±10%, TA = 0°C to +70°C; Military: Vcc = 5.0V±10%, TA

	IDT7200							A A iai			
Symbol	Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Typ.	Max.	Unit
{L (1)	Input Leakage Current (Any Input)	-1	_	1	-10		10	-1		1	μА
ILO <sup>(2)</sup> .	Output Leakage Current	-10	_	10	-10	_	10	-10		10	μA
Vон	Output Logic "1" Voltage IOH == -2mA	2.4		_	2.4		_	2.4		<del>                                     </del>	V
Vol	Output Logic "0" Voltage IoH = 8mA			0.4		_	0.4			0.4	V
ICC1 <sup>(3)</sup>	Active Power Supply Current	<del>                                     </del>	_	125 <sup>(4)</sup>	_	_	140 <sup>(4)</sup>			125 <sup>(4)</sup>	
lcc2 <sup>(3)</sup>	Standby Current (R=W=RS=FL/RT=ViH)		_	15		<del> </del>	20			15	mA
lccs(L) <sup>(3)</sup>	Power Down Current (All Input = Vcc - 0.2V)	_		0.5		_	0.9			0.5	mΑ
lcc3(S) <sup>(3)</sup>	Power Down Current (All Input = Vcc - 0.2V)	<b></b> -	-,	5			9			5	mA

2679 tbl 04

# **DC ELECTRICAL CHARACTERISTICS (Continued)**

(Commercial:  $Vcc = 5.0V\pm10\%$ ,  $TA = 0^{\circ}C$  to  $+70^{\circ}C$ ; Military:  $Vcc = 5.0V\pm10\%$ ,  $TA = -55^{\circ}C$  to  $+125^{\circ}C$ )

		IDT7200 IDT7201A IDT7202A Military ta = 30,40ns t			II II Co	DT720 DT7201 DT7202 Immer 0,65,80	A A clai				
Symbol	Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
L( <sup>(1)</sup>	Input Leakage Current (Any Input)	-10	_	10	1	_	1	-10	-	10	μА
ILO <sup>(2)</sup>	Output Leakage Current	-10	_	10	-10	-	10	-10		10	μА
Vaн	Output Logic "1" Voltage IOH = -2mA	2.4		_	2.4	=		2.4	-		V
Vol	Output Logic "0" Voltage Iон = 8mA	_	=	0.4	_	==	0.4			0.4	V
(CC1 <sup>(3)</sup>	Active Power Supply Current	_	_	140(4)	_	50	80		70	100	mΑ
ICC2 <sup>(3)</sup>	Standby Current (R=W=RS=FL/RT=VIH)			20		5	8		8	15	mA
lccs(L) <sup>(3)</sup>	Power Down Current (All Input = Vcc - 0.2V)	_	-	0.9	_		0.5			0.9	mΑ
Icca(S) <sup>(3)</sup>	Power Down Current (All Input = Vcc - 0.2V)	_	_	9	_	_	5			9	mA

#### NOTES:

- NOTES:

  1. Measurements with 0.4 ≤ ViN ≤ Vco.

  2. Ā≥ Vin, 0.4 ≤ Vouт ≤ Vco.

  3. Ico measurements are made with outputs open (only capacitive loading).

  4. Tested at f = 20MHz.

2879 tbl 05

IDT7200//201A/7202A CMOS PARALLEL FIRST-IN/FIRST-OUT FIFO 256 x 9-BIT, 512 x 9-BIT & 1K x 9-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

# **AC ELECTRICAL CHARACTERISTICS**

(Commercial: Vcc = 5.0V±10%	$_{0}$ , TA = 0°C to +70°C; Militan	y: Vcc = 5.0V±10%, Ta = -55°C to +125°C)
(Commercial, vcc = 3.0 v = 10 %	, IM = 0 0 (0 T/ 0 0, William)	y. 100 = 0.0121010, 111 = 00 0 to 1.120 =/

commerci	cial: $VCC = 5.0V\pm10\%$ , $IA = 0^{\circ}C$ to $+/0^{\circ}$	C, WIIII	ary. v	(C = 0.0	VIII 7	, IM=-	33 0 1			·		
		Comm	erclal	Com'i	& Mil.	Comm	erclal	Milit	ary	Comm	iercial	
i		7200S/L15		72009		7200S/L25		72009		7200		
ļ						7201SA 7202SA		72015/ 72025/		7201S/		
			<del></del>	72025/					Max.	Min.	Max.	Unit
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	25	Iville,	22.2	MHz
ts	Shift Frequency		40		33.3		28.5	<u> </u>	25	45	22.2	
tro	Read Cycle Time	25		30		35		40		45	35	ns
tA	Access Time		15		20		25		30		35	ns
tar	Read Recovery Time	10		10		10		10		10		ns
tapw	Read Pulse Width <sup>(2)</sup>	15		20	_	25		30		35	<u> </u>	ns
trlz	Read Pulse Low to Data Bus at Low Z <sup>(3)</sup>	5	_	5		5		5		5		ns
twlz	Write Pulse High to Data Bus at Low Z(3,4)	5		5		5		5	=	10		ns
tov	Data Valid from Read Pulse High	5		5	<u> </u>	5		5		5	<u> </u>	ns
trhz	Read Pulse High to Data Bus at High Z(3)		15		15		18		20	<u> </u>	20	ns
two	Write Cycle Time	25		30		35		40		45	<u> </u>	ns
twpw	Write Pulse Width <sup>(2)</sup>	15		20		25		30		35	<u> </u>	ns
twn	Write Recovery Time	10		10	_	10		10		10		ns
tos	Data Set-up Time	11		12		15	<u> </u>	18	<u> </u>	18		ns
ton	Data Hold Time	0	Γ-,	0		0		0		0		ns
tasc	Reset Cycle Time	25		30		35	_	40		45	_	ns
tas .	Reset Pulse Width <sup>(2)</sup>	15	-	20		25	Γ-	30		35		ns
trass	Reset Set-up Time(3)	15		20		25	-	30	_	35	_	ns
tasa	Reset Recovery Time	10	_	10	T —	10	Γ-	10	<b>—</b>	10		ns
tate	Retransmit Cycle Time	25	-	30	_	35	_	40	T —	45	T	ns
tat	Retransmit Pulse Width <sup>(2)</sup>	15	† <u> </u>	20	<b> </b>	25	<b> </b>	30		35	-	ns
tats	Retransmit Set-up Time <sup>(3)</sup>	15	<b>†</b> =	20	_	25	<b> </b>	30		35	_	ns
TRTR	Retransmit Recovery Time	10	+=	10	<b> </b>	10		10		10	<b>—</b>	ns
tEFL	Reset to Empty Flag Low	+=	25	<b> </b>	30	<del>  _</del>	35	_	40	_	45	ns
then.een	Reset to Half-Full and Full Flag High	<del>  </del>	25	<b> </b>	30	<del>  _</del>	35	_	40	-	45	ns
<del></del>	Retransmit Low to Flags Valid	+=	25	<del> </del>	30	-	35	1-	40	_	45	ns
tref tref	Read Low to Empty Flag Low	<del> </del>	15	+	20	+=	25	+_	30	1=	30	ns
taff	Read High to Full Flag High	┼ <u>-</u> -	15	+_	20	<del>  _</del>	25	<del>                                     </del>	30	<del>  -</del>	30	ns
<b> </b>	Read Pulse Width after EF High	15	╁	20	+==	25	+=	30	<u> </u>	35	<del>  -</del>	ns
TRPE	Write High to Empty Flag High	1	15	+=	20	+==	25	+==	30	+=	30	ns
twer	Write Low to Full Flag Low	+=	15	+	20	+=	25	+=	30	+=	30	ns
twff	Write Low to Half-Full Flag Low	+=	25	+=	30	<del> </del>	35	+-	40	_	45	ns
twhr	·		25	+	30	+	35	<del> </del>	40	+	45	ns
trhf	Read High to Half-Full Flag High	15	25	20	1 =	25	1 55	30	1 =	35	+ =	ns
twpf	Write Pulse Width after FF High	10	15	1 20	20		25	+=	30	+=	35	ns
txoL	Read/Write to XO Low	+		+-	20	+-	25	+=	30	+=	35	ns
txoH	Read/Write to XO High	<del> </del>	15	+=	1 20	<del> </del>	20	30	1 30	35	- 33	ns
txı	XI Pulse Width <sup>(2)</sup>	15	<del>  =</del>	20	<del>  -</del>	25	+ -		+	10	╁═	
txir	XI Recovery Time	10	<del>  -</del>	10	+-	10	<del>  -</del>	10			+-	ns
txis	XI Set-up Time	10		10		10		10		10		2679 tb



Timings referenced as in AC Test Conditions.
 Pulse widths less than minimum value are not allowed.

Values guaranteed by design, not currently tested.
 Only applies to read data flow-through mode.



2679 tbl 07

IDT7200/7201A/7202A CMOS PARALLEL FIRST-IN/FIRST-OUT FIFO 256 x 9-BIT, 512 x 9-BIT & 1K x 9-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

# **AC ELECTRICAL CHARACTERISTICS (Continued)**

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10 and a state that the state of the same is a second as		**	
(Commercial: VCC = 5.0V±10% TA = 0°C to ±70°C • M	ilitan:• \/^^ E /\/_t1/0/	TA EEOC IO	. 40E001
(Commercial: $Vcc = 5.0V\pm10\%$ , $TA = 0^{\circ}C$ to $+70^{\circ}C$ ; M	IIII ai y. VOO = 0.0 V 1076	, IA = -00°C (0	+ (200)

Comme	rcial: vcc = 5.0v±10%, TA = 0°C to +70			C = 5.0	0V±109				<u></u>			
]			itary			Comm	mercial	and Mi	litary			
			S/L40		S/L50		S/L65	7200			S/L120	1
		72025	A/LA40 A/LA40		A/LA50 A/LA50	7201SA/LA65 7202SA/LA65		7201S/ 7202S/	4/LA80 3/LA80		VLA120 VLA120	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
ts	Shift Frequency		20	_	15		12.5		10		7	MHz
tro	Read Cycle Time	50		65	<del>                                     </del>	80		100	<u> </u>	140	<del> </del>	ns
tA	Access Time		40	_	50	-	65		80	170	120	ns
tar	Read Recovery Time	10	_	15	<del></del>	15		20	<del></del>	20	120	ns
trpw	Read Pulse Width <sup>(2)</sup>	40	_	50		65	<del></del>	80	_	120		ns
trl2	Read Pulse Low to Data Bus at Low Z <sup>(3)</sup>	5	_	10		10		10		10		ns
twiz	Write Pulse High to Data Bus at Low Z(3,4)	10		15	_	15		20		20		ns
tov	Data Valid from Read Pulse High	5		5		5		5		5		ns
tanz	Read Pulse High to Data Bus at High Z <sup>(3)</sup>	-	25	_	30		30	<u> </u>	30		35	ns
two	Write Cycle Time	50	_	65		80	-	100		140		ns
twpw	Write Pulse Width <sup>(2)</sup>	40	_	50		65		80	<u> </u>	120		ns
twa	Write Recovery Time	10		15		15		20		20		ns
tos	Data Set-up Time	20		30		30		40		40		ns
toh	Data Hold Time	0	-	5		10	-	10		10	_	ns
tasc	Reset Cycle Time	50		65		80		100		140		ns
tas	Reset Pulse Width <sup>(2)</sup>	40	-	50	_	65		80		120		ns
trss	Reset Set-up Time <sup>(3)</sup>	40	_	50	_	65		80		120	<u> </u>	ns
tasa	Reset Recovery Time	10		15	_	15		20	_	20		ns
trtc	Retransmit Cycle Time	50	_	65		80		100		140		ns
<b>t</b> AT	Retransmit Pulse Width <sup>(2)</sup>	40		50		65		80		120	_	ns
tars	Retransmit Set-up Time <sup>(3)</sup>	40		50		65		80		120		ns.
<b>TATR</b>	Retransmit Recovery Time	10		15		15		20		20		ns
tefl	Reset to Empty Flag Low		50		65	_	80		100		140	ns
thfh,ffh	Reset to Half-Full and Full Flag High		50	_	65		80	<del></del>	100	_	140	ns
tate	Retransmit Low to Flags Valid	_	50		65		80		100		140	ns
IREF	Read Low to Empty Flag Low	_	30		45		60		60		60	ns
<b>TRFF</b>	Read High to Full Flag High	_	35		45		60		60		60	ns
trpe	Read Pulse Width after EF High	40		50	_	65		80	_	120		ns
twer	Write High to Empty Flag High	-	35		45	_	60		60		60	ns
twFF	Write Low to Full Flag Low	_	35	_	45		60		60		60	ns
twhF	Write Low to Half-Full Flag Low		50	_	65		80		100		140	ns
<b>t</b> RHF	Read High to Half-Full Flag High		50		65	_	80		100		140	ns
twpF	Write Pulse Width after FF High	. 40		50	_	65		80		120	_	ns
txol.	Read/Write to XO Low		40		50		65		80		120	ns
tхон	Read/Write to XO High	_	40		50		65	_	80		120	ns
txı ·	XI Pulse Width <sup>(2)</sup>	40		50		65		80		120		ns
txia	⊼i Recovery Time	10		10		10		10	_	10		ns
txis	XI Set-up Time	10		15		15		15		15		ns
NOTES:	······································											

Timings referenced as in AC Test Conditions.
 Pulse widths less than minimum value are not allowed.

Values guaranteed by design, not currently tested.
 Only applies to read data flow-through mode.

**MILITARY AND COMMERCIAL TEMPERATURE RANGES** 

## **AC TEST CONDITIONS**

AO ILOI COMPINICIO	
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load .	See Figure 1

2679 tbi 08

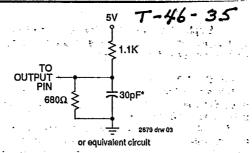


Figure 1. Output Load

\* Includes scope and jig capacitances.

## SIGNAL DESCRIPTIONS

## INPUTS:

DATA IN (Do - Ds)

Data inputs for 9-bit wide data.

#### CONTROLS:

### RESET (RS)

Reset is accomplished whenever the Reset  $(\overline{RS})$  input is taken to a low state. During reset, both internal read and write pointers are set to the first location. A reset is required after power up before a write operation can take place. Both the Read Enable  $(\overline{R})$  and Write Enable  $(\overline{W})$  inputs must be in the high state during the window shown in Figure 2, (i.e., tass before the rising edge of  $\overline{RS}$ ) and should not change until tass after the rising edge of  $\overline{RS}$ . Half-Full Flag  $(\overline{HF})$  will be reset to high after Reset  $(\overline{RS})$ .

## WRITE ENABLE (W)

A write cycle is initiated on the falling edge of this input if the Full Flag ( $\overline{FF}$ ) is not set. Data set-up and hold times must be adhered to with respect to the rising edge of the Write Enable ( $\overline{W}$ ). Data is stored in the RAM array sequentially and independently of any on-going read operation.

After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag (HF) will be set to low and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag (HF) is then reset by the rising edge of the read operation.

To prevent data overflow, the Full Flag ( $\overline{FF}$ ) will go low, inhibiting further write operations. Upon the completion of a valid read operation, the Full Flag ( $\overline{FF}$ ) will go high after tref, allowing a valid write to begin. When the FIFO is full, the internal write pointer is blocked from  $\overline{W}$ , so external changes in  $\overline{W}$  will not affect the FIFO when it is full.

## READ ENABLE (R)

A read cycle is initiated on the falling edge of the Read Enable ( $\overline{R}$ ) provided the Empty Flag ( $\overline{EF}$ ) is not set. The data is accessed on a First-In/First-Out basis, independent of any ongoing write operations. After Read Enable ( $\overline{R}$ ) goes high,

the Data Outputs (Qo – Qs) will return to a high impedance condition until the next Read operation. When all data has been read from the FIFO, the Empty Flag ( $\overline{EF}$ ) will go low, allowing the "final" read cycle but inhibiting further read operations with the data outputs remaining in a high impedance state. Once a valid write operation has been accomplished, the Empty Flag ( $\overline{EF}$ ) will go high after tWEF and a valid Read can then begin. When the FIFO is empty, the internal read pointer is blocked from  $\overline{R}$  so external changes in  $\overline{R}$  will not affect the FIFO when it is empty.

#### FIRST LOAD/RETRANSMIT (FL/RT)

This is a dual-purpose input. In the Depth Expansion Mode, this pin is grounded to indicate that it is the first loaded (see Operating Modes). In the Single Device Mode, this pin acts as the restransmit input. The Single Device Mode is initiated by grounding the Expansion In (XI).

The IDT7200/7201A/7202A can be made to retransmit data when the Retransmit Enable control (RT) input is pulsed low. A retransmit operation will set the internal read pointer to the first location and will not affect the write pointer. Read Enable (R) and Write Enable (W) must be in the high state during retransmit. This feature is useful when less than 256/512/1024 writes are performed between resets. The retransmit feature is not compatible with the Depth Expansion Mode and will affect the Half-Full Flag (HF), depending on the relative locations of the read and write pointers.

#### EXPANSION IN (XI)

This input is a dual-purpose pin. Expansion In  $(\overline{XI})$  is grounded to indicate an operation in the single device mode. Expansion In  $(\overline{XI})$  is connected to Expansion Out  $(\overline{XO})$  of the previous device in the Depth Expansion or Daisy Chain Mode.

#### **OUTPUTS:**

#### FULL FLAG (FF)

The Full Flag (FF) will go low, inhibiting further write operation, when the write pointer is one location less than the read pointer, indicating that the device is full. If the read pointer is not moved after Reset (RS), the Full-Flag (FF) will go low after 256 writes for IDT7200, 512 writes for the IDT7201A and 1024 writes for the IDT7202A.



256 x 9-BIT, 512 x 9-BIT & 1K x 9-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

IDT7200/7201A/7202A CMOS PARALLEL FIRST-IN/FIRST-OUT FIFO

EMPTY FLAG (EF)

The Empty Flag (EF) will go low, inhibiting further read operations, when the read pointer is equal to the write pointer, indicating that the device is empty.

## EXPANSION OUT/HALF-FULL FLAG (XO/HF)

This is a dual-purpose output. In the single device mode, when Expansion In (XI) is grounded, this output acts as an indication of a half-full memory.

After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag (HF) will be set low and will remain set until the difference between the write

pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag (HF) is then reset by using rising edge of the read operation.

In the Depth Expansion Mode, Expansion In (XI) is connected to Expansion Out  $(\overline{\text{XO}})$  of the previous device. This output acts as a signal to the next device in the Daisy Chain by providing a pulse to the next device when the previous device reaches the last location of memory.

## DATA OUTPUTS (Qo - Q8)

Data outputs for 9-bit wide data. This data is in a high impedance condition whenever Read  $(\overline{R})$  is in a high state.

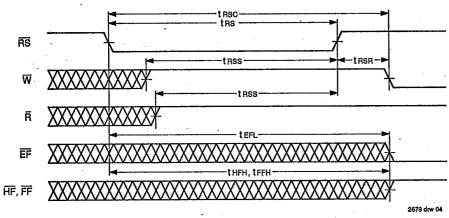


Figure 2. Reset

1. EF, FF, HF may change status during Reset, but flags will be valid at tasc.
2. W and R = V<sub>H</sub> around the rising edge of RS.

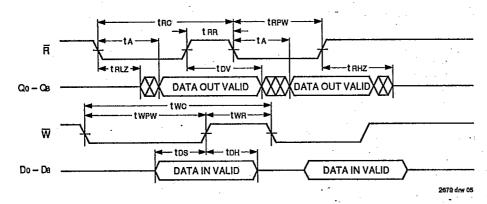


Figure 3. Asynchronous Write and Read Operation

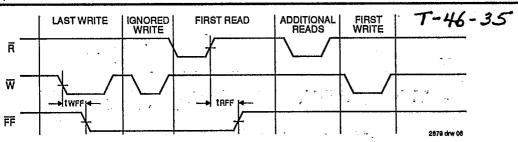
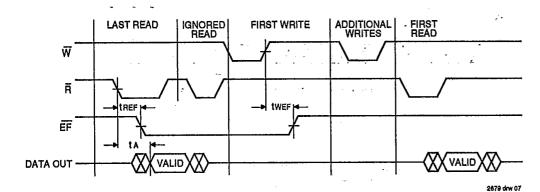


Figure 4. Full Flag From Last Write to First Read



5

Figure 5. Empty Flag From Last Read to First Write

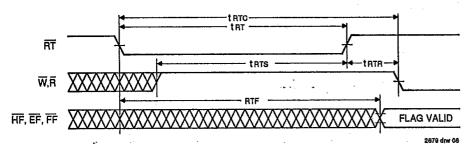


Figure 6. Retransmit

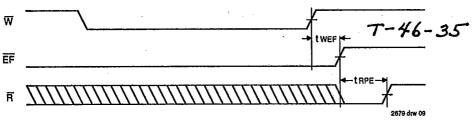


Figure 7. Minimum Timing for an Empty Flag Coincident Read Pulse

47E D

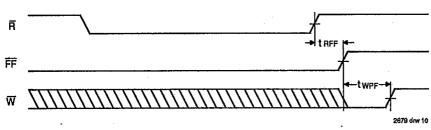


Figure 8. Minimum Timing for an Full Flag Coincident Write Pulse

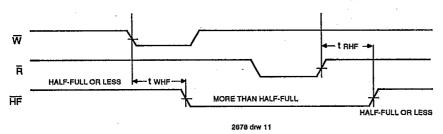


Figure 9. Half-Full Flag Timing

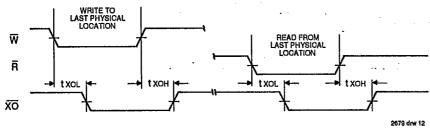


Figure 10. Expansion Out

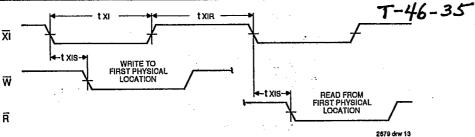


Figure 11. Expansion in

#### **OPERATING MODES:**

Care must be taken to assure that the appropriate flag is monitored by each system (i.e.  $\overline{FF}$  is monitored on the device where  $\overline{W}$  is used;  $\overline{EF}$  is monitored on the device where  $\overline{R}$  is used). For additional information, refer to Tech Note 8: Operating FIFOs on Full and Empty Boundary Conditions and Tech Note 6: Designing with FIFOs.

## Single Device Mode

A single IDT7200/7201A/7202A may be used when the application requirements are for 256/512/1024 words or less. The IDT7200/7201A/7202A is in a Single Device Configuration when the Expansion in  $(\overline{Xi})$  control input is grounded (see Figure 12).

# **Depth Expansion**

The IDT7200/7201A/7202A can easily be adapted to applications when the requirements are for greater than 256/512/ 1024 words. Figure 14 demonstrates Depth Expansion using three IDT7200/7201A/7202As. Any depth can be attained by adding additional IDT7200/7201A/7202As. The IDT7200/ 7201A/7202A operates in the Depth Expansion mode when the following conditions are met:

- 1. The first device must be designated by grounding the First Load (FL) control input.
- 2. All other devices must have  $\overline{\text{FL}}$  in the high state.
- 3. The Expansion Out  $(\overline{XO})$  pin of each device must be tied to the Expansion In (XI) pin of the next device. See Figure 14.
- External logic is needed to generate a composite Full Flag (FF) and Empty Flag (EF). This requires the ORing of all EFs and ORing of all FFs (i.e. all must be set to generate the correct composite FF or EF). See Figure 14.
- 5. The Retransmit (RT) function and Half-Full Flag (HF) are not available in the Depth Expansion Mode.

For additional information, refer to Tech Note 9: Cascading FIFOs or FIFO Modules.

### **USAGE MODES:**

#### Width Expansion

Word width may be increased simply by connecting the corresponding input control signals of multiple devices. Status flags (EF, FF and HF) can be detected from any one device. Figure 13 demonstrates an 18-bit word width by using two IDT7200/7201A/7202As. Any word width can be attained by adding additional IDT7200/7201A/7202As (Figure 13).

## **Bidirectional Operation**

Applications which require data buffering between two systems (each system capable of Read and Write operations) can be achieved by pairing IDT7200/7201A/7202As as shown in Figure 16. Both Depth Expansion and Width Expansion may be used in this mode.



#### **Data Flow-Through**

Two types of flow-through modes are permitted, a read flow-through and write flow-through mode. For the read flowthrough mode (Figure 17), the FIFO permits a reading of a single word after writing one word of data into an empty FIFO. The data is enabled on the bus in (tWEF + tA) ns after the rising edge of W. called the first write edge, and it remains on the bus until the R line is raised from low-to-high, after which the bus would go into a three-state mode after tRHZ ns. The EF line would have a pulse showing temporary deassertion and then would be asserted.

In the write flow-through mode (Figure 18), the FIFO permits the writing of a single word of data immediately after reading one word of data from a full FIFO. The R line causes the FF to be deasserted but the W line being low causes it to be asserted again in anticipation of a new data word. On the rising edge of  $\overline{W}$ , the new word is loaded in the FIFO. The  $\overline{W}$ line must be toggled when FF is not asserted to write new data in the FIFO and to increment the write pointer.

## **Compound Expansion**

The two expansion techniques described above can be applied together in a straightforward manner to achieve large FIFO arrays (see Figure 15).

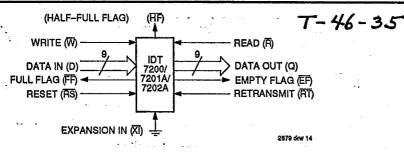


Figure 12. Block Diagram of Single 256/512/1024 x 9 FIFO

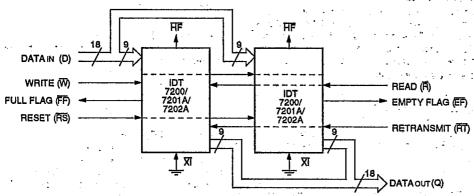


Figure 13. Block Diagram of 256/512/1024 x 18 FiFO Memory Used in Width Expansion Mode

## **TABLE I—RESET AND RETRANSMIT**

Single Device Configuration/Width Expansion Mode

		Inputs		Intern	al Status	Outputs			
Mode	AS	ĦŤ	XI	Read Pointer	Write Pointer	EF	FF	HF	
Reset	0	Х	0	Location Zero	Location Zero	0	1	1	
Retransmit	1	0	0	Location Zero	Unchanged	Х	Х	X.	
Read/Write	1	1	0	Increment <sup>(1)</sup>	Increment <sup>(1)</sup>	X	X	X	

NOTE:

2679 tbl 09

# TABLE II—RESET AND FIRST LOAD TRUTH TABLE

Depth Expansion/Compound Expansion Mode

		Inputs		Interr	nal Status	Outputs		
Mode	RS	FL.	য়	Read Pointer	Write Pointer	EF	FF	
Reset First Device	0	0	(1)	Location Zero	Location Zero	0	1	
Reset All Other Devices	0	1	(1)	Location Zero	Location Zero	0	1	
Read/Write	1	X	(1)	Х	X	X	X	

<sup>1.</sup> Pointer will increment if flag is High.

NOTE:

1. XIs connected to XO of previous device. See Figure 14. RS = Reset Input, FL/RT = First Load/Retransmit, EF = Empty Flag Output, FF = Flag Full Output, XI = Expansion Input, HF = Half-Full Flag Output

#### **MILITARY AND COMMERCIAL TEMPERATURE RANGES**

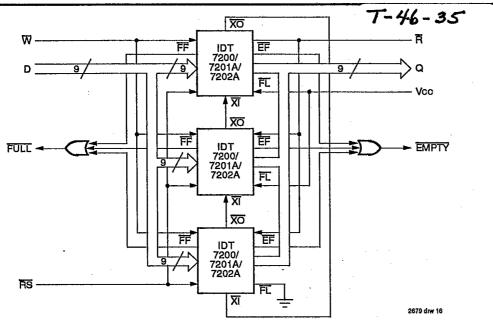


Figure 14. Block Diagram of 768 x 9/1536 x 9/3072 x 9 FiFO Memory (Depth Expansion)



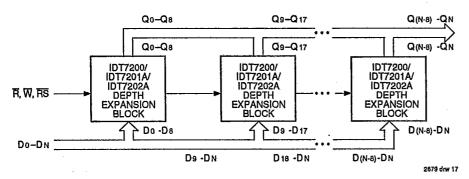


Figure 15. Compound FIFO Expansion

# NOTES:

- For depth expsansion block see section on Depth Expansion and Figure 14.
   For Flag detection see section on Width Expansion and Figure 13.

IDT7200/7201A/7202A CMOS PARALLEL FIRST-IN/FIRST-OUT FIFO 256 x 9-BIT, 512 x 9-BIT & 1K x 9-BIT

MILITARY AND COMMERCIAL TEMPERATURE RANGES

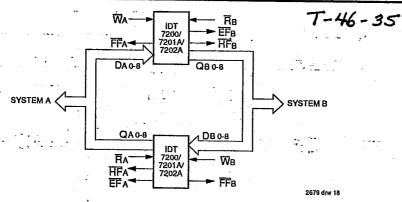


Figure 16. Bidirectional FIFO Mode

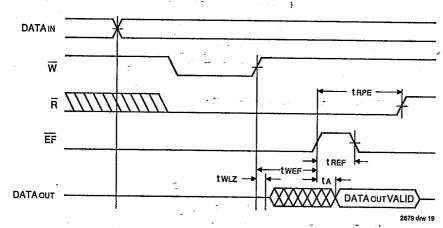


Figure 17. Read Data Flow-Through Mode

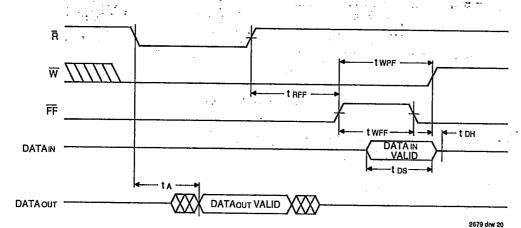


Figure 18. Write Data Flow-Through Mode